This Sheet Has Been Replaced



ABSTRACT OF THE DISCLOSURE

This invention solves the problem of a pasted SOI substrate generating voids in the peripheral part thereof and consequently decreasing the number of devices to be derived therefrom.

It concerns a method for the production of a SOI substrate obtained by pasting a first Si substrate possessing a SiO_2 surface and a second substrate possessing a Si surface on the SiO_2 surface and the Si surface, which method comprises washing the Si surface of the second Si substrate thereby imparting hydrophobicity to the Si surface before the first Si substrate and the second Si substrate are pasted together.